

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. (Currently Amended) A semiconductor wafer treatment member having at least a surface formed with a silicon carbide (SiC) film thereon, comprising a support portion for supporting a semiconductor wafer, said support portion being composed of salients with which said semiconductor wafer substantially comes into contact, and depressions formed with the silicon carbide (SiC) film to provide a coverage area between said salients, said salients being formed with upper faces having a surface roughness Ra of 0.05 μm to 1.3 μm , wherein said depressions have faces having a surface roughness Ra of 3 μm or more when measured for a length of 300 μm , wherein said coverage area has a ratio of 20 to 90 % to a total area of said depressions.

2. (Canceled).

3. (Canceled).

4. (Currently Amended) A semiconductor wafer treatment member as set forth in claim 1, wherein said top surfaces of the salients and ~~said~~ surfaces of the depressions ~~depression~~ have boundary portions in the form of curves.

5. (Currently Amended) A semiconductor wafer treatment member as set forth in ~~claim 3~~ claim 1, wherein ~~said~~ boundary portions connecting said top surfaces of the salients and said faces of the depressions are in the form of curves.

6. (Canceled).

7. (Canceled).